

100V N-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

$V_{(BR)DSS}$	Max $R_{DS(on)}$	Max I_D $T_A = 25^\circ C$ (Note 5)
100V	250m Ω @ $V_{GS} = 10V$	1.9A
	300m Ω @ $V_{GS} = 6V$	1.68A

Description and Applications

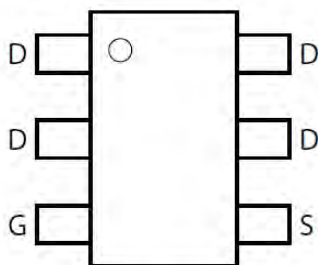
This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

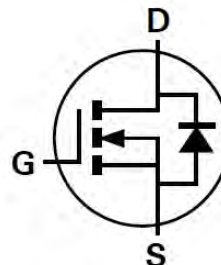
SOT26



Top View



Pinout Top-view

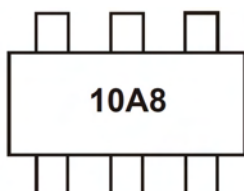


Device symbol

Ordering Information (Note 3)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN10A08E6TA	7	8	3000
ZXMN10A08E6TC	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


10A8 = Product Type Marking Code

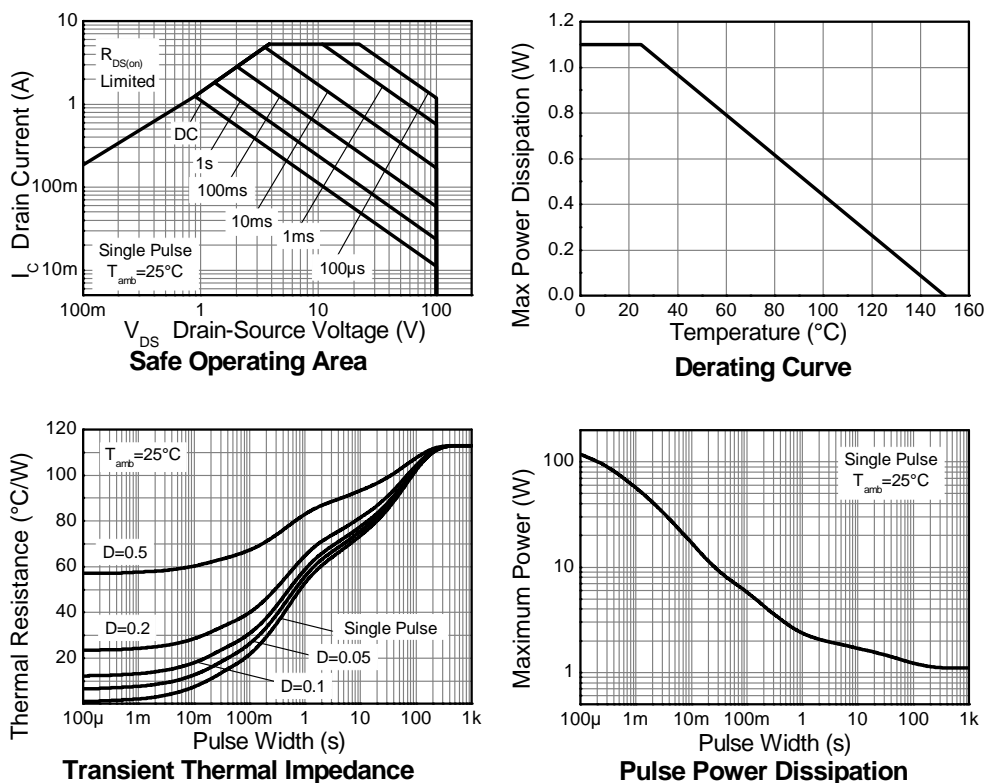
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DS}	100	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current	$V_{GS} = 10V$	Note 5)	I_D	1.9	A
		$T_A=70^{\circ}C$ (Note 5)		1.5	
		(Note 4)		1.5	
		(Note 7)		3.5	
Pulsed Drain current		(Note 6)	I_{DM}	8.6	A
Continuous Source Current (Body Diode)		(Note 5)	I_S	2.5	A
Pulsed Source Current (Body Diode)		(Note 6)	I_{SM}	8.6	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P_D	1.1	W
	(Note 5)		1.7	
	(Note 7)		6.3	
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	114	$^\circ\text{C/W}$
	(Note 5)		73.5	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{\theta JL}$	19.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 5. For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.
 6. Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.
 7. Thermal resistance from junction to solder-point (at the end of the drain lead).

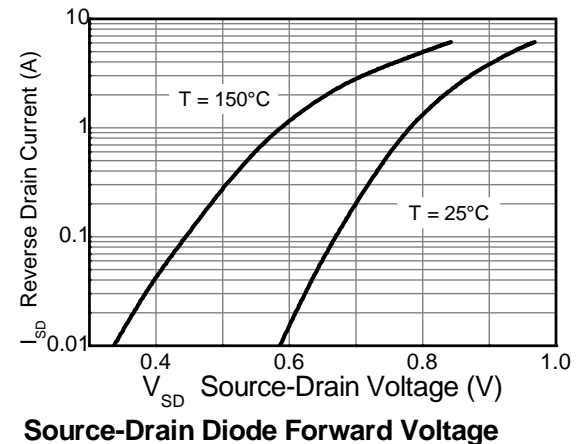
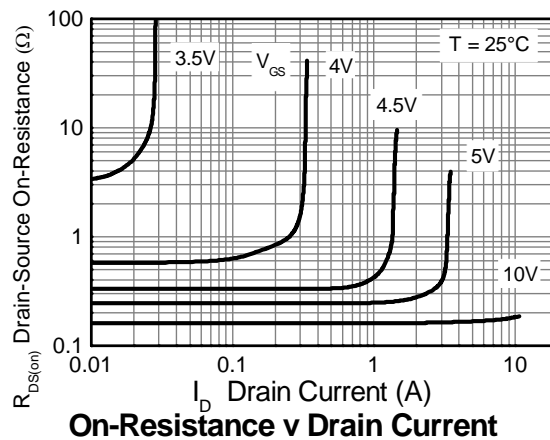
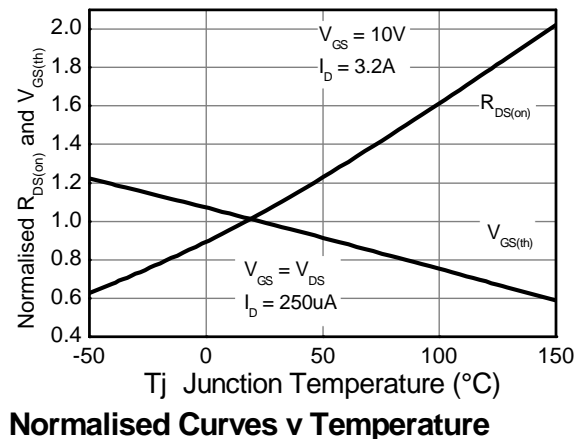
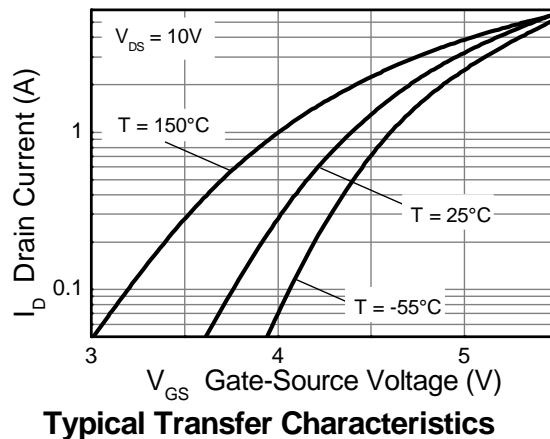
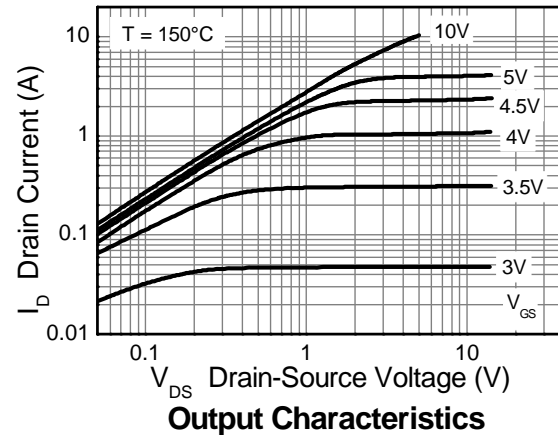
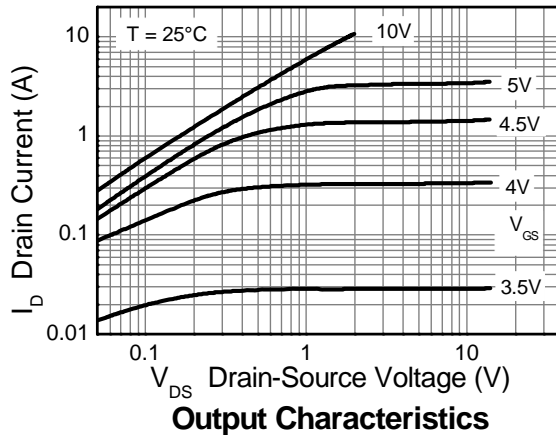
Thermal Characteristics


Electrical Characteristics @T_A = 25°C unless otherwise specified

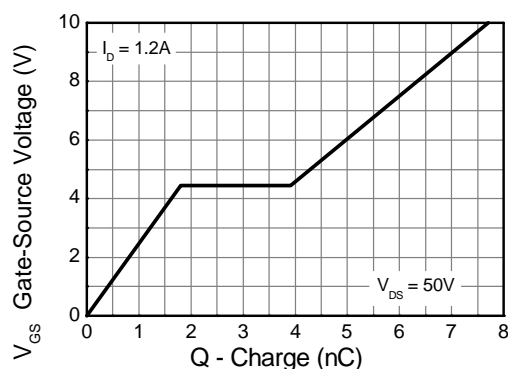
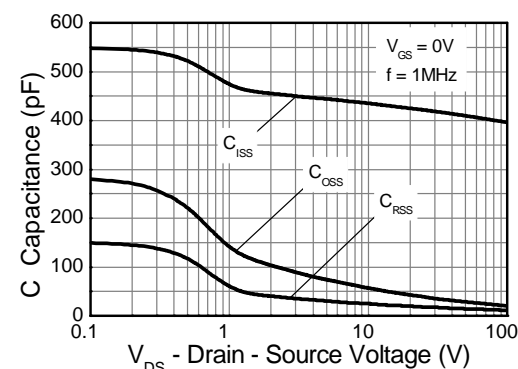
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	2.0	—	4.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 8)	R _{DS (ON)}	—	—	0.25	Ω	V _{GS} = 10V, I _D = 3.2A
				0.30		V _{GS} = 6V, I _D = 2.6A
Forward Transconductance (Notes 8 & 10)	g _{fs}	—	5.0	—	S	V _{DS} = 15V, I _D = 3.2A
Diode Forward Voltage (Note 8)	V _{SD}	—	0.87	0.95	V	I _S = 3.2A, V _{GS} = 0V
Reverse recovery time (Note 10)	t _{rr}	—	27	—	ns	I _S = 1.2A, di/dt = 100A/μs
Reverse recovery charge (Note 10)	Q _{rr}	—	32	—	nC	
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	405	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	28.2	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	14.2	—	pF	
Gate Charge (Note 9)	Q _g	—	4.2	—	nC	V _{GS} = 5V, V _{DS} = 50V I _D = 1.2A
Total Gate Charge (Note 9)	Q _g	—	7.7	—	nC	V _{GS} = 10V, V _{DS} = 50V I _D = 1.2A
Gate-Source Charge (Note 9)	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge (Note 9)	Q _{gd}	—	2.1	—	nC	
Turn-On Delay Time (Note 9)	t _{d(on)}	—	3.4	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 1.2A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	2.2	—	ns	
Turn-Off Delay Time (Note 9)	t _{d(off)}	—	8	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	3.2	—	ns	

Notes: 8. Measured under pulsed conditions. Width 300μs. Duty cycle 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

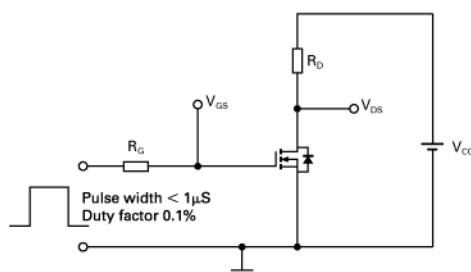
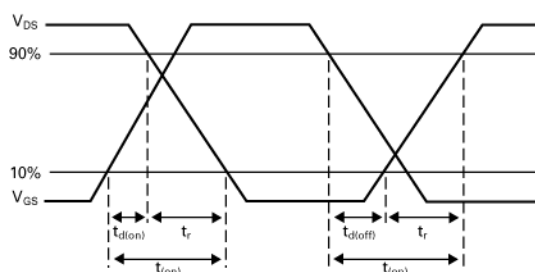
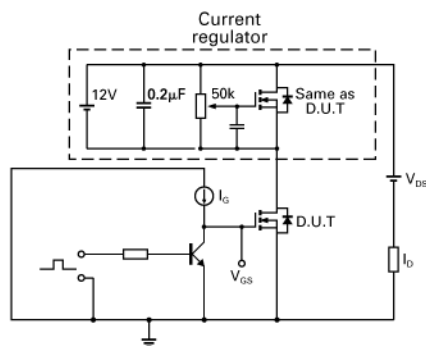
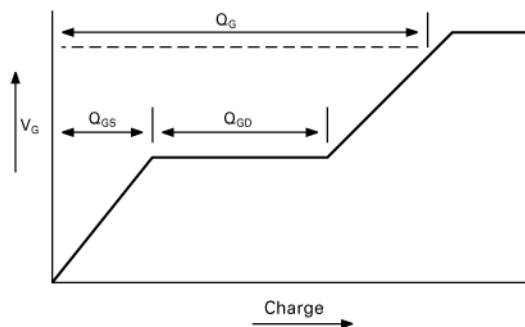
Typical characteristics



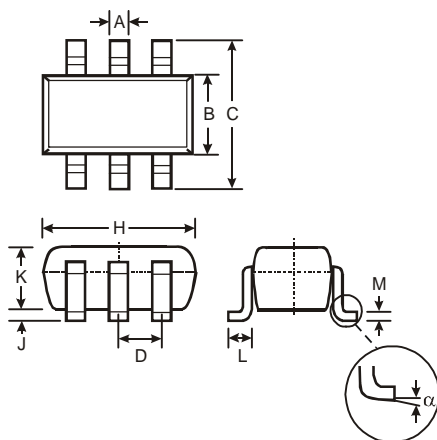
Typical characteristics - Continued



Test Circuits

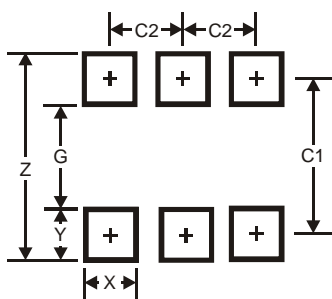


Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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